

# SGM41664

## Efficient I<sup>2</sup>C Power Backup Manager with High Current Bidirectional DC/DC Converter and Capacitor Measurement Capability

### GENERAL DESCRIPTION

The SGM41664 is a programmable power management IC with I<sup>2</sup>C interface and integrated analog-to-digital converter (ADC) for applications that need backup power or energy storage capability such as solid-state drivers (SSD). For example, in an SSD the power is needed for a few milliseconds after an unexpected supply loss to complete any remaining write action. The integrated efficient bidirectional synchronous buck converter/boost charger is capable of charging storage capacitors to as high as 36V from a 2.6V to 16V input source. A quasi-fixed frequency, constant off-time controller provides fast transient response and excellent converter stability.

An integrated reverse blocking MOSFET (RBFET) in the input allows blocking of energy leaking back to the removed source. The RBFET has a programmable current limit in the range of 1.2A to 6.2A. BUS over-voltage protection threshold is selected based on the input source nominal voltage (3.3V, 5V or 12V) by strapping the OVP pin. The I<sup>2</sup>C interface is used to set the input current limit, switching frequency, boost peak current limit and for measuring the storage capacitance and ESR. It is also used to monitor system variables and statuses, such as input voltage, input current, BUS voltage and storage voltage.

The SGM41664 is available in a green TQFN-4×4-25L package to allow compact layout design and better space saving for higher SSD memory capacity.

### APPLICATIONS

Solid-state Drivers  
Power Backup Systems

### FEATURES

- Wide 2.6V to 16V Input Voltage Range
- Up to 36V Programmable Storage Voltage
- Up to 6.2A Programmable Input Current Limit
- Efficient Bidirectional DC/DC Converter
- Low R<sub>DS(on)</sub> for Internal MOSFETs
  - ◆ Input Reverse Blocking MOSFET (RBFET): 14mΩ
  - ◆ High-side/Low-side MOSFETs: 45mΩ/60mΩ
  - ◆ STR Disconnect MOSFET (STRFET): 35mΩ
- Adjustable RBFET Turn-On Delay and Soft-Start
- Adjustable Quasi-Fixed Frequency: 0.25MHz to 1.5MHz
- Constant Off-Time Control in Steady State
- Programmable Boost Charging Peak Current
- Autonomous or I<sup>2</sup>C Modes for Optimal Operation
- Complete Voltage and Current ADC Conversion
- Selectable Input Over-Voltage Protection
- Input Reverse Blocking to Block Leakage Current
- Short-Circuit Protection at Energy Storage Side
- Storage Capacitance Measurement
- Abnormal ESR Detection

### TYPICAL APPLICATION

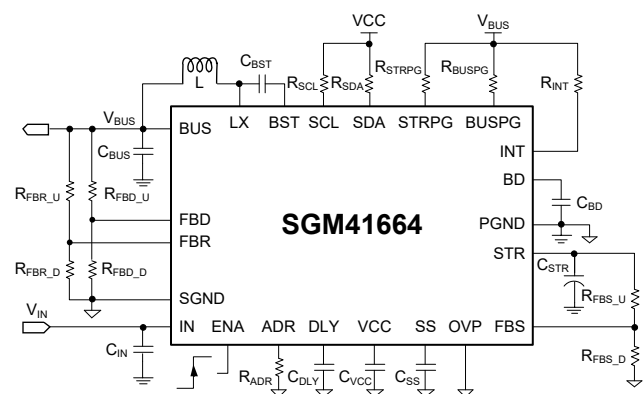


Figure 1. SGM41664 Typical Application

# Efficient Power Backup Manager with High Current Bidirectional SGM41664 DC/DC Converter and Capacitor Measurement Capability

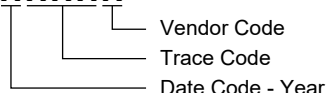
## PACKAGE/ORDERING INFORMATION

MODEL	PACKAGE DESCRIPTION	SPECIFIED TEMPERATURE RANGE	ORDERING NUMBER	PACKAGE MARKING	PACKING OPTION
SGM41664	TQFN-4×4-25L	-40°C to +125°C	SGM41664XTRQ25G/TR	SGM41664 XTRQ25 XXXXXX	Tape and Reel, 3000

## MARKING INFORMATION

NOTE: XXXXX = Date Code, Trace Code and Vendor Code.

**XXXXX**



Green (RoHS & HSF): SG Micro Corp defines "Green" to mean Pb-Free (RoHS compatible) and free of halogen substances. If you have additional comments or questions, please contact your SGMICRO representative directly.

## ABSOLUTE MAXIMUM RATINGS

Voltage Range

STR, BD, LX, BST, FBS.....	-0.3V to 38V
LX (10ns transient).....	-5V to 38V
IN, BUS, BUSPG, OVP, STRPG, ADR, FBD, FBR, ENA, BD - STR, INT.....	-0.3V to 18V
IN, BUS, BUSPG, OVP, STRPG, ADR, ENA, INT (100ns transient).....	-0.3V to 22V
SCL, SDA, DLY, SS.....	-0.3V to 6V
VCC, BST - LX.....	-0.3V to 4V

Package Thermal Resistance

TQFN-4×4-25L, $\theta_{JA}$ .....	59°C/W
Junction Temperature.....	+150°C
Storage Temperature Range.....	-65°C to +150°C
Lead Temperature (Soldering, 10s).....	+260°C

## RECOMMENDED OPERATING CONDITIONS

STR, BD, LX, BST, FBS Voltages.....	-0.3V to 36V
IN, BUS, BUSPG, OVP, STRPG, ADR, FBD, FBR, ENA, BD - STR, INT Voltages.....	-0.3V to 16V
SCL, SDA, DLY, SS Voltages.....	-0.3V to 5V
VCC, BST - LX Voltages.....	-0.3V to 3.3V
Operating Junction Temperature Range.....	-40°C to +125°C
Operating Ambient Temperature Range.....	-40°C to +125°C

## OVERSTRESS CAUTION

Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect reliability. Functional operation of the device at any conditions beyond those indicated in the Recommended Operating Conditions section is not implied.

## ESD SENSITIVITY CAUTION

This integrated circuit can be damaged if ESD protections are not considered carefully. SGMICRO recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because even small parametric changes could cause the device not to meet the published specifications.

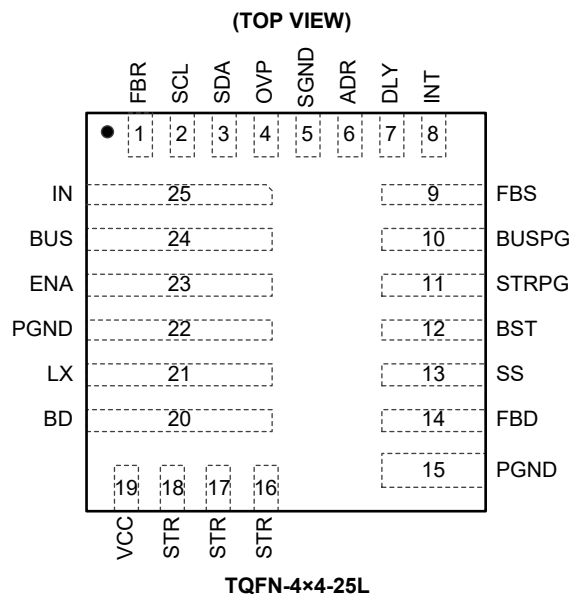
## DISCLAIMER

SG Micro Corp reserves the right to make any change in circuit design, or specifications without prior notice.

# Efficient Power Backup Manager with High Current Bidirectional DC/DC Converter and Capacitor Measurement Capability

## SGM41664

### PIN CONFIGURATION



# Efficient Power Backup Manager with High Current Bidirectional DC/DC Converter and Capacitor Measurement Capability

## SGM41664

### PIN DESCRIPTION

NUMBER	NAME	DESCRIPTION													
1	FBR	Voltage Feedback Pin for Buck Mode Regulation. Use a resistor divider to set the buck mode voltage ( $V_{REF} = 0.6V$ ).													
2	SCL	I <sup>2</sup> C Interface Clock Pin.													
3	SDA	I <sup>2</sup> C Interface Data Pin.													
4	OVP	<p>Input Over-Voltage Threshold Selection Pin (selected based on the input source voltage). Use the following table to select the input OVP threshold. Decouple the OVP pin to SGND with a 0.1μF capacitor. This pin also determines the minimum input voltage that turns on the device (POR threshold).</p> <table border="1" style="margin-left: auto; margin-right: auto;"> <thead> <tr> <th rowspan="2">OVP Pin State</th> <th rowspan="2">Input Source Voltage</th> <th>V<sub>IN</sub> OVP Threshold</th> </tr> <tr> <th>TYP</th> </tr> </thead> <tbody> <tr> <td>Low (OVP = GND)</td> <td>3.3V</td> <td>3.76V</td> </tr> <tr> <td>High (OVP = IN)</td> <td>5V</td> <td>6.03V</td> </tr> <tr> <td>OVP Floating</td> <td>12V</td> <td>14V</td> </tr> </tbody> </table>	OVP Pin State	Input Source Voltage	V <sub>IN</sub> OVP Threshold	TYP	Low (OVP = GND)	3.3V	3.76V	High (OVP = IN)	5V	6.03V	OVP Floating	12V	14V
OVP Pin State	Input Source Voltage	V <sub>IN</sub> OVP Threshold													
		TYP													
Low (OVP = GND)	3.3V	3.76V													
High (OVP = IN)	5V	6.03V													
OVP Floating	12V	14V													
5	SGND	Signal Ground Pin.													
6	ADR	I <sup>2</sup> C Address Pin. Pull ADR up by a resistor to IN pin to select address 0x59. Pull it low by a resistor to SGND to select 0x5A. Float it to select address 0x5B.													
7	DLY	Turn-On Delay Time Program Pin for the Reverse Blocking MOSFET (RBFET). Connect DLY with a capacitor ( $C_{DLY} > 10nF$ ) to SGND to program this delay time: $t_{DLY} (ms) = \frac{C_{DLY}(nF) \times 1V}{4\mu A}$ or float it for the default 1ms delay.													
8	INT	Open-Drain Interrupt Indicator Pin. INT goes high to indicate a fault condition.													
9	FBS	Voltage Feedback Pin for Energy Storage Capacitor. Use a resistor divider to set the storage voltage. If R <sub>5</sub> resistor is between STR and FBS and R <sub>6</sub> between FBS and GND, $V_{STR} = 1.2V \times (1 + R_5/R_6)$ .													
10	BUSPG	Open-Drain Power Good Output Pin for BUS Voltage. BUSPG is pulled low if FBD pin voltage drops below 0.6V, and is released to go high when the FBR pin voltage exceeds 0.63V.													
11	STRPG	Open-Drain Power Good Output Pin for STR Voltage. STRPG is pulled low if FBS pin voltage drops below 1V, and is released to go high when the FBS voltage exceeds 1.04V.													
12	BST	Bootstrap pin. It supplies the high-side gate driver of the bidirectional converter. Connect a 0.1μF or larger ceramic capacitor between this pin and LX.													
13	SS	Soft-Start Program Pin for the Reverse Blocking MOSFET. Use an external capacitor to set this soft-start time.													
14	FBD	Feedback Pin for Buck Mode Detection. The converter goes to buck mode if the FBD voltage falls below 0.6V. Use a feedback resistor divider on BUS voltage to set the BUS low voltage detection level and start buck mode.													
15, 22	PGND	Power Ground Pins.													
16, 17, 18	STR	Energy Storage Capacitor Connection Pins. Connect the storage capacitors between STR and PGND.													
19	VCC	3.3V Internal LDO output pin. Decouple VCC to GND with at least 2.2μF ceramic capacitor (X5R or better).													
20	BD	Drain Pin of the STR Disconnect FET (STRFET) and the Input of the Buck Converter. BD must be decoupled to PGND with at least 2.2μF ceramic capacitor (X5R or better).													
21	LX	Converter Switching Node Pin. Connect it to the inductor and bootstrap capacitor.													
23	ENA	Enable Control Pin for the RBFET with an internal 1MΩ pull-down resistor. Logic high enables the RBFET.													
24	BUS	BUS Output Pin. It must be decoupled to PGND with at least 22μF ceramic capacitor (X5R or better).													
25	IN	Power Supply Input Pin. Decouple it to PGND with at least 0.1μF ceramic capacitor.													

# Efficient Power Backup Manager with High Current Bidirectional DC/DC Converter and Capacitor Measurement Capability

## SGM41664

### ELECTRICAL CHARACTERISTICS

( $V_{IN} = 5V$ ,  $V_{BUS} = 5V$ ,  $L = 4.7\mu H$ ,  $V_{BD} = V_{CSTR} = 12V$ ,  $T_J = +25^\circ C$ , unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
<b>Device Power Supply (IN)</b>						
Input Voltage Range	$V_{IN}$		2.6		16	V
Input Rising for Activating I <sup>2</sup> C	$V_{IN4C}$	$V_{IN}$ rising		2.43		V
Power-On Reset (POR) Rising Threshold ( $V_{IN}$ )	$V_{PORR}$	OVP = low		2.43		V
		OVP = high		3.46		
		OVP = floating		8.4		
POR Falling Threshold ( $V_{IN}$ )	$V_{PORF}$	OVP = low		2.3		V
		OVP = high		3.26		
		OVP = floating		7.9		
On-Resistance of RBFET	$R_{DSON\_R}$			14		m $\Omega$
Reverse Blocking Leakage Current	$I_{RBLK}$	$V_{IN} = 0V$ , $V_{BUS} = 16V$ , $V_{ENA} = 0V$		0.1		$\mu A$
		$V_{IN} = 16V$ , $V_{BUS} = 0V$ , $V_{ENA} = 0V$		0.1		
Input Supply Current Before POR	$I_{IN\_POR}$	$V_{IN}$ rises to 8V, OVP = floating, ENA = high, $-40^\circ C < T_J < +125^\circ C$		165		$\mu A$
Bias Current (IN)	$I_{BIAS}$	$V_{IN} = 5V$ , OVP = high, DC/DC converter is disabled		1280		$\mu A$
Reverse Blocking Range	$V_{RB}$				16	V
Input Over-Voltage Threshold	$V_{OVP}$	OVP = low		3.76		V
		OVP = high		6.03		
		OVP = floating		14		
Input Over-Voltage Threshold Hysteresis	$V_{OVPHYS}$	OVP = low		150		mV
		OVP = high		200		
		OVP = floating		400		
RBFET Turn-On Delay Time	$t_{DLY}$	$C_{DLY} = 10nF$ <sup>(1)</sup>		2.5		ms
Soft-Start Time	$t_{SS}$	$C_{SS} = 100nF$ <sup>(2)</sup>		20.6		ms
Current Limit Program Range	$I_{LIM}$		1.2		6.2	A
Current Limit Accuracy		LSP[5:3] = 011		$\pm 10\% I_{LIM}$		
BUSPG Threshold	$V_{BUSPGH}$	$V_{FBR}$ rising		0.63		V
	$V_{BUSPGL}$	$V_{FBD}$ falling		0.6		V
Internal LDO Output Voltage	$V_{VCC}$	$V_{IN} > 3.3V$		3.25		V
		$V_{IN} \leq 3.3V$		$V_{IN}$		
ENA Logic Voltage	$V_{ENAH}$			0.85		V
	$V_{ENAL}$			0.74		V
OVP Pin Logic Voltage	$V_{OVPH}$			0.9		V
	$V_{OVPL}$			0.6		V
<b>Bidirectional DC/DC Converter</b>						
BUS Side Operation Voltage Range	$V_{BUSOP}$		2.6		16	V
STR Side Buck Operation Voltage Range	$V_{STROP}$		2.6		36	V
Boost Minimum Peak Current	$I_{PMIN}$			210		mA
Switching Frequency	$f_{SWBST}$	SF[1:0] = 01		500		kHz
Minimum LSFET On-Time	$t_{OFF\_MINL}$	During boost/buck mode		110		ns
Minimum HSFET On-Time	$t_{ON\_MIN}$	During boost/buck mode		110		ns
Boost CV Mode Voltage Reference	$V_{REF\_BST}$			1.2		V

# Efficient Power Backup Manager with High Current Bidirectional SGM41664 DC/DC Converter and Capacitor Measurement Capability

## ELECTRICAL CHARACTERISTICS (continued)

( $V_{IN} = 5V$ ,  $V_{BUS} = 5V$ ,  $L = 4.7\mu H$ ,  $V_{BD} = V_{CSTR} = 12V$ ,  $T_J = +25^\circ C$ , unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
$V_{FBS}$ Boost Burst Mode Stop Switching Threshold	$V_{BRT\_R}$	$V_{FBS}$ rising		1.2		V
$V_{FBS}$ Boost Burst Mode Switching Resume Threshold	$V_{BRT\_F}$	$V_{FBS}$ falling		1.17		V
$V_{FBS}$ Boost Burst Mode Threshold Accuracy				2.5		%
$V_{FBD}$ Buck Detection Voltage Reference	$V_{BUCK\_DET}$	$V_{FBD}$ falling		0.6		V
$V_{FBD}$ Buck Regulation Voltage Reference	$V_{BUCK\_REG}$			0.6		V
Maximum Cycle-by-Cycle Buck Peak Current	$I_{PK\_BK}$			7		A
$V_{FBS}$ STRPG Threshold	$V_{STRPGH}$	$V_{FBS}$ rising		1.04		V
	$V_{STRPGL}$	$V_{FBS}$ falling		1		V
STR Short-Circuit Detection Threshold in Pre-charge	$V_{STRSC}$	$V_{FBS}$ value		0.7		V
Pre-charge Current	$I_{PRECHG}$			133		mA
$R_{DSON}$ of High-side FET	$R_{DSON\_H1}$			45		m $\Omega$
$R_{DSON}$ of Low-side FET	$R_{DSON\_L1}$			60		m $\Omega$
$R_{DSON}$ of STR Disconnect FET	$R_{DSON\_D}$			35		m $\Omega$
<b>STR Capacitor Measurement</b>						
Capacitance Measurement Discharge Current	$I_{DIS}$	DCP[7:6] = 01		5		mA
Internal Counter Clock	$f_{CLK}$			500		Hz
Abnormal ESR Detection Discharge Current	$I_{ESR}$			0.8		A
<b>I<sup>2</sup>C and Logic Interfaces (SDA, SCL, ADR, INT)</b>						
High State Input Voltage	$V_{IH}$	SDA and SCL pins		1.3		V
Low State Input Voltage	$V_{IL}$	SDA and SCL pins		0.7		V
Low State Output Voltage	$V_{OL}$	Sink 4mA, SDA and INT pins		TBD		V
ADR Pin Logic Voltage	$V_{ADRH}$			0.9		V
	$V_{ADRL}$			0.6		V
<b>ADC</b>						
ADC Reference Voltage	$V_{REF\_ADC}$			1		V
ADC Resolution				8		Bits
ADC Conversion Time		For one variable		40		$\mu s$
<b>Thermal Protection</b>						
Thermal Shutdown Temperature	$T_{SD}$			150		$^\circ C$
Thermal Recovery Hysteresis	$T_{HYS}$			25		$^\circ C$
Thermal Warning Threshold	$T_{WRN}$			125		$^\circ C$

NOTES:

### 1. Recommended Delay Time Program Table

$C_{DLY}$ (nF)	None	10	47	100
Delay Time (ms)	1.0	2.5	11.8	25

### 2. Recommended Soft-Start Time Program Table

$C_{SS}$ (nF)	None	10	47	100
Rise Time (ms)	1.0	2.1	9.7	20.6

# Efficient Power Backup Manager with High Current Bidirectional DC/DC Converter and Capacitor Measurement Capability

## SGM41664

### REGISTER ADDRESS MAP (17, 8-Bit Registers)

REGISTER NAME	ADDRESS	BIT NAME AND DEFAULT VALUE							
		D7	D6	D5	D4	D3	D2	D1	D0
Vendor ID	0x00	Reserved	Reserved	Reserved (or Device Revision)			Reserved	Reserved	Reserved
		0	0	0	0	0	0	0	0
RBFET Control Parameter Programming	0x01	V <sub>IN</sub> OVP Enable	Reserved	Input Current Limit Threshold			Reserved	Reserved	ENA
		0	0	1	1	1	0	0	1
DC/DC Converter Control Parameter Programming	0x02	C <sub>STR</sub> Measurement Discharge Current	Reserved	Reserved	Boost Peak Current			ENCON	
		1	1	0	0	1	0	0	1
Buck-Off Voltage Programming	0x03	Buck Off Voltage Programming							
		0	0	1	1	0	1	1	1
VDIS1 Programming	0x04	V <sub>DIS1</sub> Threshold Programming							
		1	0	1	0	0	1	1	0
VDIS2 Programming	0x05	V <sub>DIS2</sub> Threshold Programming							
		1	0	0	0	1	1	1	1
Switching Frequency, C <sub>STR</sub> Measuring, Reverse Block and CV Mode Programming	0x06	Reserved	Reverse Block Enable	C <sub>STR</sub> Measurement Enable	Boost CV Mode Enable	C <sub>STR</sub> ESR Detection Threshold		Switching Frequency	
		0	0	0	0	0	0	0	1
C <sub>STR</sub> Discharge Timer High Byte	0x07	High Byte of C <sub>STR</sub> Discharge Timer Results							
		0	0	0	0	0	0	0	0
C <sub>STR</sub> Discharge Timer Low Byte	0x08	Low Byte of C <sub>STR</sub> Discharge Timer Results							
		0	0	0	0	0	0	0	0
ADC I <sub>IN</sub> Data and ESR Detection Status	0x09	ADC Input Current Data						Reserved	C <sub>STR</sub> ESR Condition Status
		0	0	0	0	0	0	0	0
ADC V <sub>BUS</sub> Data	0x0A	ADC V <sub>BUS</sub> Data							
		0	0	0	0	0	0	0	0
STR OVP Programming	0x0B	Reserved	Reserved	Reserved	V <sub>STR</sub> OVP Threshold Programming				
		0	0	0	1	1	1	0	1
ADC V <sub>IN</sub> Data	0x0C	ADC V <sub>IN</sub> Data							
		0	0	0	0	0	0	0	0
ADC V <sub>STR</sub> Data	0x0D	ADC V <sub>STR</sub> Data							
		0	0	0	0	0	0	0	0
Interrupt Mask Control	0x0E	V <sub>IN</sub> OVP Mask	Input OCP Mask	C <sub>STR</sub> SCP Mask	Reverse Blocking Protection Mask	C <sub>STR</sub> Measure Complete Mask	ADC Complete Mask	High T <sub>J</sub> Warning Mask	Thermal Shutdown Mask
		0	0	0	0	0	0	0	0
Interrupt Flag	0x0F	V <sub>IN</sub> OVP Flag	Input OCP Flag	C <sub>STR</sub> SCP Flag	Reverse Blocking Protection Flag	C <sub>STR</sub> Measure Complete Flag	ADC Complete Flag	High T <sub>J</sub> Warning Flag	Thermal Shutdown Flag
		0	0	0	0	0	0	0	0
System Control	0x10	ADC Converting Enable	Reserved	V <sub>IN</sub> Recovery Mode	Thermal Shutdown Mode	V <sub>STR</sub> OVP Interrupt Flag	V <sub>BUS</sub> Power Fail Interrupt Flag	V <sub>IN</sub> Power Good Flag	RBFET Status Flag
		0	0	0	0	0	0	1	0

# Efficient Power Backup Manager with High Current Bidirectional SGM41664 DC/DC Converter and Capacitor Measurement Capability

## REGISTER DESCRIPTION

Slave device address is selectable among **0x59**, **0x5A** and **0x5B**.

**R:** Read only bit

**R/W:** Read or write bit

### Vendor ID Register (Address: 0x00)

BITS	BIT NAME	DESCRIPTION	COMMENT	PORV	TYPE
D[7]	CTRL[7]	Reserved		0	R
D[6]	CTRL[6]	Reserved		0	R
D[5]	CTRL[5]	Reserved (or Device Revision)		0	R
D[4]	CTRL[4]			0	R
D[3]	CTRL[3]			0	R
D[2]	CTRL[2]	Reserved		0	R
D[1]	CTRL[1]	Reserved		0	R
D[0]	CTRL[0]	Reserved		0	R

### RBFET Control Parameter Programming Register (Address: 0x01)

BITS	BIT NAME	DESCRIPTION	COMMENT	PORV	TYPE
D[7]	LSP[7]	V <sub>IN</sub> OVP Enable Bit 0 = OVP function is enabled (default) 1 = OVP function is disabled		0	R/W
D[6]	LSP[6]	Reserved		0	R
D[5]	LSP[5]	Input Current Limit Threshold 000 = 1.2A 001 = 2A 010 = 2.5A 011 = 3A 100 = 3.5A 101 = 4A 110 = 4.5A 111 = 6.2A (default)		1	R/W
D[4]	LSP[4]			1	R/W
D[3]	LSP[3]			1	R/W
D[2]	LSP[2]	Reserved		0	R
D[1]	LSP[1]	Reserved		0	R
D[0]	LSP[0]	ENA Bit 0 = RBFET is disabled 1 = RBFET is enabled (default)		1	R/W



# Efficient Power Backup Manager with High Current Bidirectional SGM41664 DC/DC Converter and Capacitor Measurement Capability

## REGISTER DESCRIPTION (continued)

**DC/DC Converter Control Parameter Programming Register (Address: 0x02)**

BITS	BIT NAME	DESCRIPTION	COMMENT	PORV	TYPE
D[7]	DCP[7]	C <sub>STR</sub> Measurement Discharge Current 00 = 2mA 01 = 5mA 10 = 10mA 11 = 20mA (default)		1	R/W
D[6]	DCP[6]			1	R/W
D[5]	DCP[5]	Reserved		0	R
D[4]	DCP[4]	Reserved		0	R
D[3]	DCP[3]	Boost Peak Current 000 = 300mA 001 = 500mA 010 = 600mA 011 = 800mA 100 = 1A (default) 101 = 1.5A 110 = 2A 111 = 2.5A		1	R/W
D[2]	DCP[2]			0	R/W
D[1]	DCP[1]			0	R/W
D[0]	DCP[0]	ENCON, DC/DC Converter Enable Bit 0 = DC/DC converter is disabled 1 = DC/DC converter is enabled (default)		1	R/W

**Buck-Off Voltage Programming Register (Address: 0x03)**

BITS	BIT NAME	DESCRIPTION	COMMENT	PORV	TYPE
D[7]	OFF[7]	Buck-Off Voltage Programming	Default: 0x37. V <sub>BUCK_OFF</sub> = 2.64V  V <sub>BUCK_OFF</sub> = OFF[7:0] × 0.048V The V <sub>BUCK_OFF</sub> program range is 2.64V to 12V.  Example: If OFF[7:0] = 0x37, then V <sub>BUCK_OFF</sub> = (3 × 16 <sup>1</sup> + 7 × 16 <sup>0</sup> ) × 0.048 = 2.64V.	0	R/W
D[6]	OFF[6]			0	R/W
D[5]	OFF[5]			1	R/W
D[4]	OFF[4]			1	R/W
D[3]	OFF[3]			0	R/W
D[2]	OFF[2]			1	R/W
D[1]	OFF[1]			1	R/W
D[0]	OFF[0]			1	R/W

**VDIS1 Programming Register (Address: 0x04)**

BITS	BIT NAME	DESCRIPTION	COMMENT	PORV	TYPE
D[7]	VDIS1[7]	V <sub>DIS1</sub> Threshold Programming (For C <sub>STR</sub> measurement)	Default: 0xA6. V <sub>DIS1</sub> = 24.9V  V <sub>DIS1</sub> = VDIS1[7:0] × 0.15V The V <sub>DIS1</sub> voltage program range is 1.5V to 36V.  Example: If VDIS1[7:0] = 0xA6, then V <sub>DIS1</sub> = (10 × 16 <sup>1</sup> + 6 × 16 <sup>0</sup> ) × 0.15 = 24.9V.	1	R/W
D[6]	VDIS1[6]			0	R/W
D[5]	VDIS1[5]			1	R/W
D[4]	VDIS1[4]			0	R/W
D[3]	VDIS1[3]			0	R/W
D[2]	VDIS1[2]			1	R/W
D[1]	VDIS1[1]			1	R/W
D[0]	VDIS1[0]			0	R/W

# Efficient Power Backup Manager with High Current Bidirectional DC/DC Converter and Capacitor Measurement Capability

## SGM41664

### REGISTER DESCRIPTION (continued)

#### VDIS2 Programming Register (Address: 0x05)

BITS	BIT NAME	DESCRIPTION	COMMENT	PORV	TYPE
D[7]	VDIS2[7]	V <sub>DIS2</sub> Threshold Programming (For C <sub>STR</sub> measurement)	Default: 0x8F. V <sub>DIS2</sub> = 21.45V  V <sub>DIS2</sub> = VDIS2[7:0] × 0.15V The V <sub>DIS2</sub> voltage program range is 1.5V to 36V.  Example: If VDIS2[7:0] = 0x8F, then V <sub>DIS2</sub> = (8 × 16 <sup>1</sup> + 15 × 16 <sup>0</sup> ) × 0.15 = 21.45V.	1	R/W
D[6]	VDIS2[6]			0	R/W
D[5]	VDIS2[5]			0	R/W
D[4]	VDIS2[4]			0	R/W
D[3]	VDIS2[3]			1	R/W
D[2]	VDIS2[2]			1	R/W
D[1]	VDIS2[1]			1	R/W
D[0]	VDIS2[0]			1	R/W

#### Switching Frequency, C<sub>STR</sub> Measuring, Reverse Block and CV Mode Program Register (Address: 0x06)

BITS	BIT NAME	DESCRIPTION	COMMENT	PORV	TYPE
D[7]	SF[7]	Reversed		0	R
D[6]	SF[6]	Reverse Block Enable Bit 0 = RBFET turns off once the reverse current exceeds 0.5A 1 = RBFET unchanged if the reverse current exceeds 0.5A		0	R/W
D[5]	SF[5]	C <sub>STR</sub> Measurement Enable Default: 0	Capacitance measurement starts when SF[5] changes from 0 to 1.	0	R/W
D[4]	SF[4]	Boost CV Mode Enable 0 = CV mode (Default) 1 = Burst mode		0	R/W
D[3]	SF[3]	C <sub>STR</sub> ESR Detection Threshold 00 = 50mV (default) 01 = 100mV 10 = 150mV 11 = 200mV		0	R/W
D[2]	SF[2]			0	R/W
D[1]	SF[1]	Switching Frequency 00 = 250kHz 01 = 500kHz (default) 10 = 1MHz 11 = 1.5MHz		0	R/W
D[0]	SF[0]			1	R/W

#### C<sub>STR</sub> Discharge Timer High Byte Register (Address: 0x07)

BITS	BIT NAME	DESCRIPTION	COMMENT	PORV	TYPE
D[7]	TIMH[7]	1 = 65536ms	Capacitor Discharge Timer Reading Range: 0 - 131070ms	0	R
D[6]	TIMH[6]	1 = 32768ms		0	R
D[5]	TIMH[5]	1 = 16384ms		0	R
D[4]	TIMH[4]	1 = 8192ms		0	R
D[3]	TIMH[3]	1 = 4096ms		0	R
D[2]	TIMH[2]	1 = 2048ms		0	R
D[1]	TIMH[1]	1 = 1024ms		0	R
D[0]	TIMH[0]	1 = 512ms		0	R

# Efficient Power Backup Manager with High Current Bidirectional SGM41664 DC/DC Converter and Capacitor Measurement Capability

## REGISTER DESCRIPTION (continued)

**C<sub>STR</sub> Discharge Timer Low Byte Register (Address: 0x08)**

BITS	BIT NAME	DESCRIPTION	COMMENT	PORV	TYPE
D[7]	TIML[7]	1 = 256ms	Capacitor Discharge Timer Reading Range: 0 - 131070ms	0	R
D[6]	TIML[6]	1 = 128ms		0	R
D[5]	TIML[5]	1 = 64ms		0	R
D[4]	TIML[4]	1 = 32ms		0	R
D[3]	TIML[3]	1 = 16ms		0	R
D[2]	TIML[2]	1 = 8ms		0	R
D[1]	TIML[1]	1 = 4ms		0	R
D[0]	TIML[0]	1 = 2ms		0	R

**ADC I<sub>IN</sub> Data and ESR Detection Status Register (Address: 0x09)**

BITS	BIT NAME	DESCRIPTION	COMMENT	PORV	TYPE
D[7]	LSC[7]	1 = 4.8A	Input Current ADC Results Reading Range: 0 - 9.45A 6 bits (0 - 63) × 0.15A resolution	0	R
D[6]	LSC[6]	1 = 2.4A		0	R
D[5]	LSC[5]	1 = 1.2A		0	R
D[4]	LSC[4]	1 = 0.6A		0	R
D[3]	LSC[3]	1 = 0.3A		0	R
D[2]	LSC[2]	1 = 0.15A		0	R
D[1]	LSC[1]	Reserved		0	R
D[0]	LSC[0]	Detected ESR Status (ESR <sub>CSTR</sub> ) 0 = ESR normal 1 = ESR error	Error is detected if the $\Delta V_{STR}$ (= ESR × I <sub>ESR</sub> ) is higher than the threshold set in SF[3:2] bits.	0	R

**ADC V<sub>BUS</sub> Data Register (Address: 0x0A)**

BITS	BIT NAME	DESCRIPTION	COMMENT	PORV	TYPE
D[7]	BUS[7]	1 = 8.192V	V <sub>BUS</sub> ADC Results Reading Range: 0 - 16.32V 8 bits (0 - 255) × 64mV resolution	0	R
D[6]	BUS[6]	1 = 4.096V		0	R
D[5]	BUS[5]	1 = 2.048V		0	R
D[4]	BUS[4]	1 = 1.024V		0	R
D[3]	BUS[3]	1 = 0.512V		0	R
D[2]	BUS[2]	1 = 0.256V		0	R
D[1]	BUS[1]	1 = 0.128V		0	R
D[0]	BUS[0]	1 = 0.064V		0	R

# Efficient Power Backup Manager with High Current Bidirectional SGM41664 DC/DC Converter and Capacitor Measurement Capability

## REGISTER DESCRIPTION (continued)

### STR Over-Voltage Protection Programming Register (Address: 0x0B)

BITS	BIT NAME	DESCRIPTION	COMMENT	PORV	TYPE
D[7]	OVP[7]	Reserved		0	R
D[6]	OVP[6]	Reserved		0	R
D[5]	OVP[5]	Reserved		0	R
D[4]	OVP[4]	V <sub>STR</sub> OVP Threshold Programming	Default: 0x1D, V <sub>STROVP</sub> = 36V The V <sub>STROVP</sub> voltage program range is 7V to 38V.  V <sub>STROVP</sub> = OVP[4:0] × 1V+ 7V Example: if OVP[4:0] = 0x1D, then V <sub>STROVP</sub> = (1 × 16 <sup>1</sup> + 13 × 16 <sup>0</sup> + 7) × 1 = 36V.	1	R/W
D[3]	OVP[3]			1	R/W
D[2]	OVP[2]			1	R/W
D[1]	OVP[1]			0	R/W
D[0]	OVP[0]			1	R/W

### ADC V<sub>IN</sub> Data Register (Address: 0x0C)

BITS	BIT NAME	DESCRIPTION	COMMENT	PORV	TYPE
D[7]	IN[7]	1 = 8.192V	V <sub>IN</sub> ADC Results Reading Range: 0 - 16.32V 8 bits (0 - 255) × 64mV resolution	0	R
D[6]	IN[6]	1 = 4.096V		0	R
D[5]	IN[5]	1 = 2.048V		0	R
D[4]	IN[4]	1 = 1.024V		0	R
D[3]	IN[3]	1 = 0.512V		0	R
D[2]	IN[2]	1 = 0.256V		0	R
D[1]	IN[1]	1 = 0.128V		0	R
D[0]	IN[0]	1 = 0.064V		0	R

### ADC V<sub>STR</sub> Data Register (Address: 0x0D)

BITS	BIT NAME	DESCRIPTION	COMMENT	PORV	TYPE
D[7]	STR[7]	1 = 19.2V	V <sub>STR</sub> ADC Results Reading Range: 0 - 38.25V 8 bits (0 - 255) × 0.15V resolution	0	R
D[6]	STR[6]	1 = 9.6V		0	R
D[5]	STR[5]	1 = 4.8V		0	R
D[4]	STR[4]	1 = 2.4V		0	R
D[3]	STR[3]	1 = 1.2V		0	R
D[2]	STR[2]	1 = 0.6V		0	R
D[1]	STR[1]	1 = 0.3V		0	R
D[0]	STR[0]	1 = 0.15V		0	R

# Efficient Power Backup Manager with High Current Bidirectional SGM41664 DC/DC Converter and Capacitor Measurement Capability

## REGISTER DESCRIPTION (continued)

### Interrupt (INT Pin Output Signal) Mask Control Register (Address: 0x0E)

BITS	BIT NAME	DESCRIPTION	COMMENT	PORV	TYPE
All		0 = event can assert interrupt 1 = event cannot interrupt but its flag bit is set		0	R/W
D[7]	MASK[7]	Mask $V_{IN}$ OVP Interrupt	If $V_{IN}$ OVP function is enabled in LSP[7].	0	R/W
D[6]	MASK[6]	Mask Input OCP Interrupt		0	R/W
D[5]	MASK[5]	Mask $C_{STR}$ SCP Interrupt		0	R/W
D[4]	MASK[4]	Mask Reverse Blocking Protection Interrupt	If the RB protection is enabled in SF[6].	0	R/W
D[3]	MASK[3]	Mask $C_{STR}$ Measurement Complete Interrupt	Measuring starts if SF[5] rises from 0 to 1.	0	R/W
D[2]	MASK[2]	Mask ADC Complete Interrupt	ADC starts when SYS[7] rises from 0 to 1.	0	R/W
D[1]	MASK[1]	Mask High Junction Temperature Warning Interrupt		0	R/W
D[0]	MASK[0]	Mask Thermal Shutdown Interrupt		0	R/W

### Interrupt Flag Register (Address: 0x0F)

BITS	BIT NAME	DESCRIPTION	COMMENT	PORV	TYPE
All		0 = event has not occurred 1 = event has occurred To reset flag and interrupt, write 1 to the bit after the event is cleared.		0	R/W
D[7]	FLAG[7]	$V_{IN}$ OVP Event Flag Bit ( $V_{IN}$ OVP exceeded)	If $V_{IN}$ OVP function is enabled in LSP[7].	0	R/W
D[6]	FLAG[6]	Input OCP Event Flag Bit (Input current limit exceeded)		0	R/W
D[5]	FLAG[5]	$C_{STR}$ SCP Event Flag Bit ( $V_{STR}$ fell below the short-circuit threshold)		0	R/W
D[4]	FLAG[4]	Reverse Blocking Protection Event Flag Bit (BUS to IN current passed the reverse current threshold).	If the RB protection is enabled in SF[6].	0	R/W
D[3]	FLAG[3]	$C_{STR}$ Measurement Complete Event Flag Bit	Measuring starts if SF[5] rises from 0 to 1.	0	R/W
D[2]	FLAG[2]	ADC Conversion Complete Event Flag Bit	ADC starts if SYS[7] rises from 0 to 1.	0	R/W
D[1]	FLAG[1]	High Junction Temperature Warning Event Flag Bit ( $T_J > +125^{\circ}\text{C}$ )		0	R/W
D[0]	FLAG[0]	Thermal Shutdown Event Flag Bit ( $T_J > +150^{\circ}\text{C}$ )		0	R/W

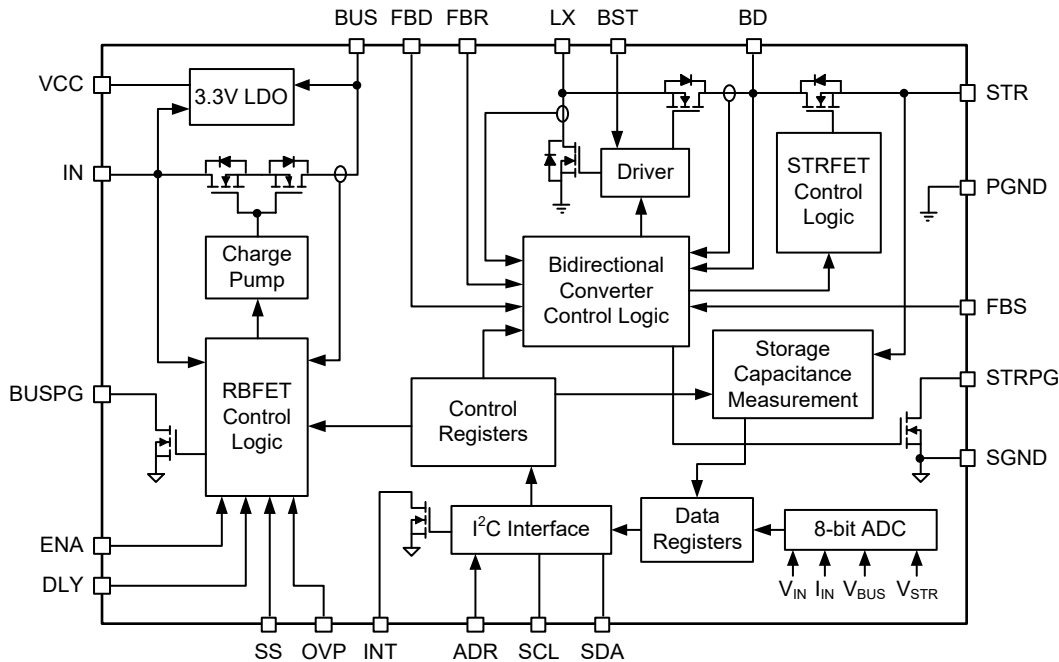
### System Control Register (Address: 0x10)

BITS	BIT NAME	DESCRIPTION	COMMENT	PORV	TYPE
D[7]	SYS[7]	ADC Conversion Enable Default: 0	ADC starts if SYS[7] rises from 0 to 1.	0	R/W
D[6]	SYS[6]	Reserved		0	R
D[5]	SYS[5]	Converter Mode After $V_{IN}$ Recovery 0 = Run and continue in buck mode until $V_{BUS}$ goes below $V_{PORF}$ 1 = Exit buck mode and charge $C_{BUS}$ from $V_{IN}$ (if already in buck mode)		0	R/W
D[4]	SYS[4]	After Detecting Thermal Shutdown 0 = Force to buck mode 1 = Turn off all circuits immediately		0	R/W
D[3]	SYS[3]	$V_{STR}$ OVP Flag Bit and Interrupt 0 = No $V_{STR}$ OVP event occurred 1 = $V_{STR}$ passed the $V_{STROVP}$ threshold. An interrupt is asserted. To reset the flag and interrupt, write 1 to the bit after the event is cleared.		0	R/W
D[2]	SYS[2]	$V_{BUS}$ Power Fail Flag Bit and Interrupt 0 = No $V_{BUS}$ power fail event occurred 1 = $V_{FBD}$ fell below $V_{BUCK\_DET}$ threshold. An interrupt is asserted. To reset the flag and interrupt, write 1 to the bit after the event is cleared.		0	R/W
D[1]	SYS[1]	$V_{IN}$ Power Good Flag Bit and Interrupt 0 = $V_{IN}$ source not good. An interrupt is asserted. This flag is automatically set to 1 and interrupt is reset after a good $V_{IN}$ is detected. 1 = Good $V_{IN}$ source is detected		1	R
D[0]	SYS[0]	RBFET Status Flag Bit 0 = RBFET is off 1 = RBFET is on		0	R

# Efficient Power Backup Manager with High Current Bidirectional DC/DC Converter and Capacitor Measurement Capability

## SGM41664

### FUNCTIONAL BLOCK DIAGRAM



**Figure 2. Block Diagram**

### DETAILED DESCRIPTION

The SGM41664 is a cost effective power management device for applications that need power backup or energy storage. The stored energy can be delivered to system to complete urgent tasks if the input source has failed. For example, an SSD can complete its write after unexpected power removal. This device includes a synchronous bidirectional buck converter that in the reverse direction (boost) acts as an efficient charger for energy storage capacitors (STR) and in the forward direction (buck) releases energy from the storage capacitors into the BUS. An I<sup>2</sup>C interface and an ADC are also integrated for monitoring of the parameters, system status and flexible device configuration.

The input power supply and the load (system) are connected to the input (IN) and the BUS, respectively. Normally, the source (IN) directly connects to the BUS through the integrated reverse blocking MOSFET (RBFET). The BUS is linked to the storage capacitors on the STR pin through the bidirectional DC/DC converter BD port and a disconnecting switch (STRFET). When  $V_{IN}$  is normal, the STR capacitors are kept charged at a high voltage level using the bidirectional converter in boost mode. In case of a sudden source shutdown like  $V_{IN}$  removal, the converter acts in buck mode and discharges the backup capacitors to the BUS to hold the  $V_{BUS}$  voltage up and disconnects the RBFET to avoid leaking of energy to the failed input.

#### Startup Sequence

The startup has several steps. It is started when the  $V_{IN}$  exceeds the 2.43V threshold. The internal LDO and bias circuits are turned on and the I<sup>2</sup>C interface is initialized for communication. All 17 registers will also reset to their default values. If the input voltage drops below 2.3V, the LDO, bias circuits and I<sup>2</sup>C interface will be turned off.

The host can access the registers after the power-on reset (POR) is completed. POR has 3 steps for input:

1. LDO (VCC) Power up.
2. Poor Source Qualification.
3. Turning RBFET on to connect  $V_{IN}$  to BUS.

## DETAILED DESCRIPTION (continued)

To allow RBFET turn-on, the source voltage and current supply capabilities must qualify the following criteria:

1.  $V_{IN} > V_{PORR}$  when pulling 20mA for a period of  $t_{DLY}$ .
2.  $V_{IN} < V_{OVP}$ .

$V_{OVP}$  and  $V_{PORR}$  are programmed by strapping OVP to IN, SGND or leaving OVP floating, depending on the application input voltage (3.3V, 5V or 12V). If an OVP fault is detected ( $V_{IN} > V_{OVP}$ ), the device waits until this condition is cleared and then recovers automatically. If a poor source is detected (condition1), the source qualification routine is repeated every 300ms.

After input qualification, the  $V_{IN}$  power good flag is set (SYS[1] = 1), and the RBFET turn-on process starts with a delay timing ( $t_{DLY}$ ) if  $V_{IN} > V_{BUS}$  and both ENA pin and ENA bit are set, that is:

1. External ENA = H (ENA pin is pulled high).
2. Internal ENA bit is set, LSP[0] = 1 (default).
3.  $V_{IN} > V_{BUS}$ .

If all above conditions are valid and after the  $t_{DLY}$  is passed, the RBFET gradually turns on and charges the BUS capacitors from 0V to  $V_{IN}$  with a controlled rate (soft-start,  $t_{SS}$ ). The soft-start time is set by the  $C_{SS}$  capacitor on the SS pin. Finally, when the SS pin voltage reaches 1.4V, the boost converter can be enabled by the DCP[0] bit for charging the backup capacitors. The capacitor on the BD pin is also charged during the soft-start period.

After the soft-start time, if the converter-enable bit DCP[0] is set, the pre-charge period will start when  $V_{FBR} > 0.63V$ . In this period, the boost output (BD voltage) is regulated in the range of 120% to 135% of the  $V_{BUS}$  and the STR capacitors are charged with a pre-charge current near 133mA. The pre-charge period ends when the STRFET voltage (between BD and STR) is almost 0. At this time the STRFET is fully turned on and the boost converter starts to regulate the FBS voltage.

The DLY pin is provided to set  $t_{DLY}$ . If it is floating, the  $t_{DLY}$  is about 1ms. If a capacitor ( $C_{DLY}$ ) is connected to DLY pin, it will be charged with a 4 $\mu$ A current source and the time between 0V to 1V determines the  $t_{DLY}$  time, estimated by Equation 1:

$$t_{DLY} \text{ (ms)} = \frac{C_{DLY} \text{ (nF)} \times 1V}{4\mu A} \quad (1)$$

After the  $t_{DLY}$  time, the  $V_{BUS}$  soft-start time ( $t_{SS}$ ) begins. The SS pin programs this time. If the SS pin is left floating,  $t_{SS}$  is about 1ms. If a capacitor ( $C_{SS}$ ) is connected to the SS pin, it will be charge by a 6.8 $\mu$ A current source and the time between 0V to 1.4V determines the  $t_{SS}$  time, estimated by Equation 2:

$$t_{SS} \text{ (ms)} = \frac{C_{SS} \text{ (nF)} \times 1.4V}{6.8\mu A} \quad (2)$$

### Converter Control in Charger Mode (Boost)

After completing the RBFET soft-start, and  $V_{FBR} > 0.63V$ , the bidirectional converter starts to operate as a boost charger with constant off-time peak current control. The peak is programmed in the DCP[3:1] bits through I<sup>2</sup>C interface.

At the beginning of each cycle in boost mode, the low-side MOSFET (LSFET) is turned on and the inductor current starts to rise until it reaches the programmed peak value. At this point the LSFET turns off and HSFET turns on. The inductor current starts to decrease while flowing through the STRFET to the STR capacitor. After a fixed off time, the LSFET is turned on again and the next cycle starts. The STR voltage is set by the divider resistor connected to the FBS feedback pin.

The boost operation can be set to the high efficiency burst mode (SF[4] = 1) or to the low-ripple constant voltage (CV) mode (SF[4] = 0). In burst mode, the boost charger stops switching when the FBS voltage reaches 1.2V and starts again when it falls below 1.17V. In CV mode, the LSFET turns on for a new cycle only if the  $V_{FBS}$  is below the 1.2V reference. Otherwise, it remains off until  $V_{FBS}$  falls below 1.2V.

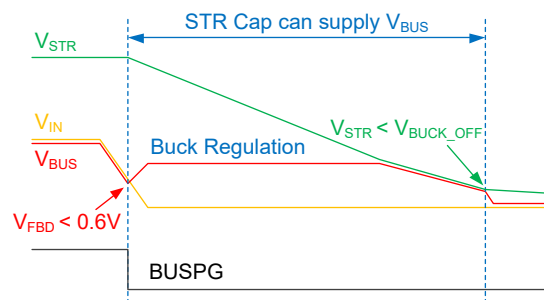
## DETAILED DESCRIPTION (continued)

The default peak current for boost mode is set to 1A (DCP[3:1] bits = 100) but it can be programmed to 7 other values between 0.3A to 2.5A. For the values lower than 0.8A (0.3A, 0.5A or 0.6A), the HSFET will not turn on in the off-time (only the body diode conducts) to reduce the negative peak current of the inductor. Even for the peak currents above 0.8A, the inductor current can go negative due to the minimum on-time of the HSFET that may result in the STR voltage not reaching the programmed voltage at high conversion ratios. Therefore, higher peak currents such that ( $I_{PEAK} > \Delta I_L/2$ ) are recommended. The typical  $t_{ON\_MIN}$  for the HSFET is 80ns. The following equation can be used to choose the proper boost peak current setting.

$$I_{PEAK} (A) \geq \frac{V_{STR}(V) - V_{IN}(V)}{2 \times L(\mu H)} \times 80(ns) \quad (3)$$

### Converter Control in Buck Mode

The buck mode is activated as soon as a significant  $V_{BUS}$  drop is detected ( $V_{FBD}$  falling below 0.6V) to use the backup energy. Upon detection of  $V_{FBD} < 0.6V$ , the converter starts operating as a buck and the RBFET is turned off to block negative current from  $V_{BUS}$  to  $V_{IN}$ . The SYS[0] is also set to 0 to show the RBFET shutdown status. In buck mode, the energy stored in the STR capacitors is transferred to the BUS capacitors using a quasi-fixed frequency constant off-time control scheme for faster response. In buck mode the BUS regulation voltage is set by FBR pin. The maximum peak current in buck mode is internally clamped to 7A. When the STR voltage falls below the buck-off threshold ( $V_{BUCK\_OFF}$ ) programmed in OFF[7:0] bits, switching stops and the buck shuts down. The detailed shutdown process waveforms and transfer of the stored energy to the BUS after an unexpected input removal is shown in Figure 3.



**Figure 3. Use of Backup Energy to Keep the System Powered for a Short Time before Shutdown after an Unexpected Input Removal**

### Startup after Input Recovery

SYS[5] bit can be used to select the recovery mode when  $V_{IN}$  returns to normal. If SYS[5] = 0, after input recovery, the converter temporarily continues in buck mode to discharge any remaining charge in the STR capacitor and waits for  $V_{BUS}$  to drop below  $V_{PORF}$ . Then a new startup sequence with POR will start.

If SYS[5] = 1, the source qualification is performed if  $V_{IN} > V_{PORR}$ . After qualification, the  $V_{IN}$  power good flag (SYS[1]) is set to 1 and RBFET is turned fully on. If the buck mode is still on, it will end if all of the following conditions are valid:

1. ENA pin = H (pulled high).
2. ENA bit (LSP[0]) = 1.
3.  $V_{BUS} < V_{IN} < V_{OVP}$ .
4.  $V_{BUS} > V_{PORF}$ .
5.  $T_J < +125^\circ C$ .

The input POR falling/rising thresholds ( $V_{PORF}/V_{PORR}$ ) and the input OVP threshold ( $V_{OVP}$  and  $V_{OVPHYS}$ ) are set by strapping the OVP pin (IN, SGND, or floating).



## DETAILED DESCRIPTION (continued)

### Control of the Reverse Blocking FET

The RBFET unit controls the input current limiting, over-voltage (OV) protection and reverse blocking (RB) functions. If any of the following 8 conditions occurs, the RBFET is softly turned off, the SYS[0] bit is set to 0, and the converter enters buck mode:

1.  $V_{IN}$  voltage falls below  $V_{PORF}$ .
2. ENA bit (LSP[0]) = 0 or ENA pin = L (pulled low).
3.  $V_{FBD}$  falls below 0.6V.
4. Reverse current from BUS to IN exceeds 500mA if reverse block enable bit (SF[6]) is 0.
5. Input OV triggers if  $V_{IN}$  OVP enable bit (LSP[7]) is 0.
6. Input current exceeds  $I_{LIM}$  threshold.
7. Thermal shutdown is detected if thermal shutdown mode setting bit SYS[4] is 0.
8. Converter operates in buck mode.

### Device Enable and Disable

The ENA pin and the ENA bit (LSP[0]) can enable or disable the device. The internal circuits are enabled if both of them are high. It is recommended to pull up the ENA pin by two 100k $\Omega$  resistors to both IN and BUS pins.

### VCC Output

The internal circuits are powered from the LDO that is supplied from the higher of  $V_{IN}$  or  $V_{BUS}$ . A 2.2 $\mu$ F or larger ceramic capacitor is required on the LDO output (VCC pin) for decoupling. The normal VCC voltage is 3.3V. If the device is powered from a 3.3V or lower source, the VCC will follow  $V_{IN}$  due to the required headroom. In this condition, any external loading on VCC such as a small BUSPG pull-up resistor can pull the VCC down and cause startup issues. Therefore, use 100k $\Omega$  pull-up resistors for BUSPG, STRPG and INT or pull them up to the BUS pin instead, if  $V_{BUS}$  is 5V or less.

### BUS Power Good (BUSPG)

The BUSPG is an open-drain output pin with 4mA pull-down capability. If  $V_{FBD}$  drops below 0.6V, the BUSPG is pulled low. When  $V_{FBR}$  exceeds 0.63V, it is released to go high. Pull the BUSPG up with a 100k $\Omega$  resistor to BUS (if  $V_{BUS} \leq 5V$ ) or VCC.

### STR Power Good (STRPG)

The STRPG is an open-drain output pin with 4mA pull down capability. If  $V_{FBS}$  pin falls below 1V, the STRPG is pulled low and when  $V_{FBS}$  exceeds 1.04V, it is released to go high. Pull the STRPG up with a 100k $\Omega$  resistor to BUS (if  $V_{BUS} \leq 5V$ ) or VCC.

### Internal ADC

An integrated 8-bit analog-to-digital converter (ADC) measures the  $V_{IN}$ ,  $I_{IN}$ ,  $V_{BUS}$  and  $V_{STR}$  continuously in the boost mode only. The A/D conversion is started by setting the SYS[7] bit from 0 to 1. When the conversions are complete, the FLAG[2] bit is set to 1. An interrupt signal is also asserted, if it is not masked. There is no A/D conversion in buck mode.

See the ADC register descriptions for details.

The SGM41664 enters buck mode as soon as any of the following events occurs during the A/D conversion:

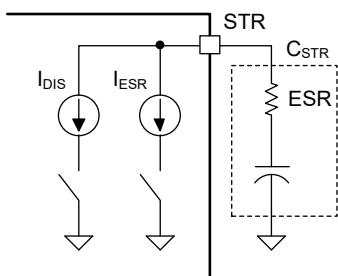
1.  $V_{IN}$  drops below  $V_{PORF}$ .
2. Disabling the device (LSP[0] = 0 or ENA pulled low).
3.  $V_{FBD}$  falls below 0.6V.
4. Input OVP event (if  $V_{IN}$  OVP is enabled, LSP[7] = 0).
5.  $I_{IN}$  exceeds  $I_{LIM}$  threshold.
6. BUS to IN reverse current exceeds 500mA (if the reverse block is enabled, SF[6] = 0).
7. Thermal shutdown (if the thermal shutdown mode setting bit, SYS[4], is 0).

**DETAILED DESCRIPTION (continued)**

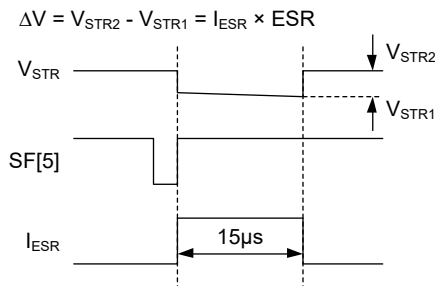
**Measuring the Storage Capacitor**

The SGM41664 can measure the  $C_{STR}$  capacitance and ESR by two internal current sinks as shown in Figure 4. The ESR detection current ( $I_{ESR}$ ) is almost 0.8A, and the  $C_{STR}$  detection current ( $I_{DIS}$ ) can be set to 2mA, 5mA, 10mA or 20mA (default) by DCP[7:6] bits. The measuring steps are as follows with ESR measured first:

1. The  $C_{STR}$  measurement-complete-interrupt bit must be unmasked by setting MASK[3] to 0.
2. The host initiates the measurement by creating a 0 to 1 transition in the SF[5] bit.
3.  $C_{STR}$  is charged until  $V_{FBS}$  reaches 1.2V.
4.  $C_{STR}$  is discharged by  $I_{ESR}$  for 15 $\mu$ s and  $V_{STR}$  is measured just before and after turning  $I_{ESR}$  off. The voltage difference will be equal to  $ESR \times I_{ESR}$ .
5. If the difference is higher than the programmed ESR detection threshold set by SF[3:2] bits, an ESR error is identified and the LSC[0] is set to 1. See Figure 5 for the ESR detection process.

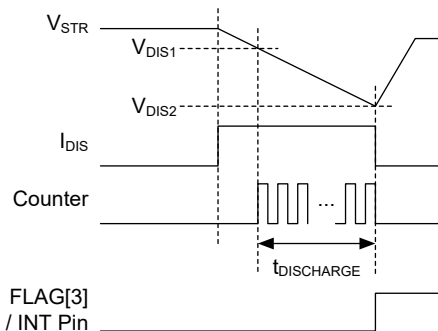


**Figure 4. Capacitance and ESR Measuring Circuit**



**Figure 5. ESR Measurement Process**

6. After completing the ESR detection, the  $I_{DIS}$  current sink is turned on to discharge  $C_{STR}$ .
7. A 500kHz counter measures the discharge time when STR voltage falls from  $V_{DIS1}$  to  $V_{DIS2}$  as shown in Figure 6 and then the  $I_{DIS}$  is turned off.  $V_{DIS1}$  and  $V_{DIS2}$  are set in the registers REG0x04 and REG0x05 with 24.9V and 21.45V default values, respectively. The 16-bit discharge time data ( $t_{DISCHARGE}$ ) is stored in the registers REG0x07 and REG0x08.
8. After completing the measurement, boost charging function is restarted automatically and FLAG[3] is set to 1. An interrupt is also asserted if it is unmasked.



**Figure 6. Measuring Capacitance with 500kHz Counter**

## DETAILED DESCRIPTION (continued)

9. To reset the FLAG[3], a '1' must be written to it.

10.  $t_{DISCHARGE}$  is read from the registers REG0x07 and REG0x08 to calculate the  $C_{STR}$  from Equation 4:

$$C_{STR} = \frac{I_{DIS} \times t_{DISCHARGE}}{V_{DIS1} - V_{DIS2}} \quad (4)$$

For example, if REG0x07 = 01h and REG0x08 = 23h, then  $t_{DISCHARGE} = 291 (0123h) \times 2 = 582ms$ . If  $V_{DIS1} = 24.9V$ ,  $V_{DIS2} = 21.45V$  and  $I_{DIS} = 20mA$ , The  $C_{STR}$  will be  $3374\mu F$ :

$$C_{STR} = \frac{I_{DIS} t_{DISCHARGE}}{V_{DIS1} - V_{DIS2}} = \frac{20mA \times 582ms}{24.9V - 21.45V} = 3374\mu F$$

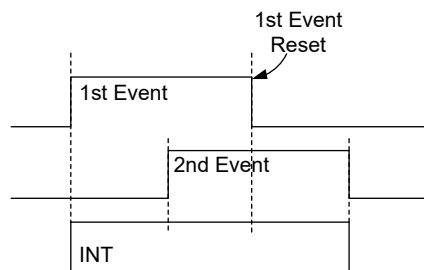
$V_{DIS1}$  and  $V_{DIS2}$  must be larger than  $V_{IN}$ .

The device will switch to buck mode if any of the following events occurs during measurement. The STR capacitor cannot be measured in buck mode.

1.  $V_{IN}$  drops below  $V_{PORF}$ .
2. Disabling the device (LSP[0] = 0 or ENA pulled low).
3.  $V_{FBD}$  falls below 0.6V.
4. Input OVP (if  $V_{IN}$  OVP is enabled, LSP[7] = 0).
5.  $I_{IN}$  exceeds  $I_{LIM}$  threshold.
6. BUS to IN reverse current exceeds 500mA (if the reverse block is enabled, SF[6] = 0).
7. Thermal shutdown (if the thermal shutdown mode setting bit, SYS[4], is 0)

### Interrupt and Event Sequence Control

The INT pin is an open-drain output. A 100kΩ pull-up resistor to BUS pin (if  $V_{BUS} \leq 5V$ ) or VCC is recommended. It goes high if a fault condition occurs and is not masked. The interrupt informs the host that a fault has occurred. The INT remains high until it is reset by the host. If a new interrupt occurs before reset, it remains high until all events are reset by the host as shown in Figure 7.



**Figure 7. Interrupt Control Sequence**

Table 1 summarizes the fault events and the actions that happen after their interrupts.

### Input Over-Voltage Protection (OVP)

The OVP pin can be tied to IN or SGND, or left open to select one of the 3 input OVP thresholds ( $V_{OVP}$ ). Refer to the PIN DESCRIPTION table for details.

If the  $V_{IN}$  OVP detection is enabled (LSP[7] = 0), then a  $V_{IN}$  OVP fault is detected when  $V_{IN}$  exceeds the  $V_{OVP}$  threshold. Upon OVP detection, the RBFET is turned off and the buck converter starts to operate to maintain the  $V_{BUS}$  power from the stored energy in the STR capacitor. FLAG[7] holds the  $V_{IN}$  OVP status until it is reset by the host. The OVP asserts an interrupt if it is not masked.

## DETAILED DESCRIPTION (continued)

### Input Over Current Protection (OCP)

An input current limiter controls the input current in the RBFET to avoid inrush current from IN to BUS. The SS external capacitor sets the soft-start time to control the charge rate of the BUS capacitors and limits the inrush current. The input current limit is set by LSP[5:3] bits. When the input is qualified, the current starts to ramp from 0A and is kept below the programmed input current limit during the soft-start time.

If the  $I_{IN}$  reaches the OCP threshold, the RBFET is turned off and the buck converter starts to maintain  $V_{BUS}$  from the storage capacitors. An interrupt is asserted if it is not masked and the input OCP event flag (FLAG[6]) is set to record the OCP event status.

### BUS and STR Short-Circuit Protection (SCP)

If a short circuit happens on the BUS during the normal operation, the RBFET will shut down immediately and the converter enters buck mode to discharge the storage capacitor with maximum peak current. The BUS power fail event flag (SYS[2]) is also set to record the event and an interrupt is asserted.

If a BUS short circuit occurs before POR is completed, while  $V_{BUS}$  is below 90% of  $V_{IN}$  and soft-start time is completed, the RBFET is turned off and an interrupt signal is asserted. The SYS[2] flag is also set to record the event. Then the RBFET waits for  $2 \times t_{SS}$  before a new soft-start begins automatically.

STR voltage is continuously checked from 56ms after the pre-charge process begins. In the pre-charge period, an STR short circuit is identified, if  $V_{STR}$  cannot exceed 0.7V. Upon detection of an STR short, the STRFET is turned off and the converter stops switching. Also, the  $C_{STR}$  SCP event flag (FLAG[5]) is set to record the SCP event and an interrupt is asserted (if not masked). After an STR short, the converter latches off and a new power-on cycle (and POR) will automatically start only if  $V_{BUS}$  drops below  $V_{PORF}$ , or the device is disabled or enabled.

During the fast charge period, an STR short event is identified if the  $V_{STR}$  drops below 0.7V or  $V_{BUS} - 0.2V$ . During the STR capacitance measurement the STR short circuit detection is disabled. When the converter is in buck mode, the STR to BUS voltage drop detection is disabled.

### Reverse Blocking Protection (RBP)

The RBFET reverse blocking protection is activated when the current from BUS to  $V_{IN}$  reaches 500mA if the reverse block enable bit, SF[6], is set to 1. The RBFET is also turned off and the buck converter starts to maintain  $V_{BUS}$ . The SYS[0] bit is also set to 0 to record the RBFET shutdown status and the RBP flag, FLAG[4], is set to record this event. An interrupt is also asserted if it is not masked. RBP is disabled if SF[6] = 0.

### STR Over-Voltage Protection (STR OVP)

When  $V_{STR}$  exceeds the threshold set by OVP[4:0] bits, an STR OVP occurs and the boost charger stops switching. The STR OVP event flag, SYS[3], is set and an interrupt is asserted. The boost charger is restarted when the  $V_{STR}$  drops 1V below the STR OVP threshold.

### Thermal Warning and Shutdown

A thermal warning feature is implemented in the device to avoid thermal runaway. If the die temperature ( $T_J$ ) exceeds +125°C, the high  $T_J$  warning flag (FLAG[1]) is set to 1 and an interrupt asserted (if it is not masked). Writing a 1 to this bit resets the interrupt after  $T_J$  falls below +100°C.

Similarly, if the junction temperature reaches +150°C, the thermal shutdown bit (FLAG[0]) is set to 1 and an interrupt is asserted if it is unmasked.

Two thermal shutdown response types can be selected by SYS[4] bit. If SYS[4] = 1, all circuits will turn off immediately. If SYS[4] = 0, the device is forced into buck mode with RBFET in off state and discharges the  $C_{STR}$  into  $C_{BUS}$  until  $V_{STR}$  falls below  $V_{BUCK\_OFF}$  and the buck is turned off. The device will recover automatically when  $T_J$  falls below +125°C similar to a  $V_{IN}$  recovery. Writing 1 to the FLAG[0] resets the interrupt after  $T_J$  drops below +125°C. If the junction temperature rises to +150°C, all circuits will turn off.

# Efficient Power Backup Manager with High Current Bidirectional SGM41664 DC/DC Converter and Capacitor Measurement Capability

## DETAILED DESCRIPTION (continued)

### Default Register Values

All control registers have a fixed default value that is loaded after power-on reset. They can be modified after power-on through the I<sup>2</sup>C interface and by the host to meet the system requirements. The device I<sup>2</sup>C address can be set by the ADR pin. Refer to the PIN DESCRIPTION table for detailed.

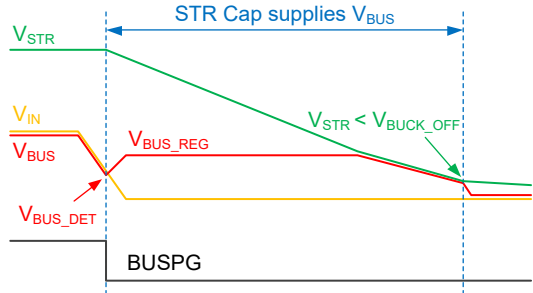
**Table 1. Fault Events and Responses**

Event	Flag Bit	Indicator(s)	Power Action After Event
Input Over Voltage	V <sub>IN</sub> OVP Flag FLAG[7] bit	INT pin goes high	V <sub>IN</sub> OVP is enabled by LSP[7] bit. RBFET turns off and IC enters buck mode.
Input Over Current	Input OCP Flag FLAG[6] bit	INT pin goes high	RBFET turns off. IC enters buck mode.
C <sub>STR</sub> Short Circuit	C <sub>STR</sub> SCP Flag FLAG[5] bit	INT pin goes high STRPG pin goes low	STRFET turns off. Converter switching stops.
Reverse Current (From BUS to IN)	Reverse Blocking Protection Flag FLAG[4] bit	INT pin goes high	Reverse blocking protection is enabled by SF[6] bit. RBFET turns off and IC enters buck mode.
C <sub>STR</sub> Measurement Complete	C <sub>STR</sub> Measurement Complete Flag FLAG[3] bit	INT pin goes high	No action
ADC Complete	ADC Conversion Complete Flag FLAG[2] bit	INT pin goes high	No action.
Junction High Temperature	High T <sub>J</sub> Warning Flag FLAG[1] bit	INT pin goes high	No action.
Junction Over Temperature	Thermal Shutdown Flag FLAG[0] bit	INT pin goes high	RBFET turns off. If SYS[4] is 0, IC enters buck mode. Otherwise all circuits are turned off.
V <sub>STR</sub> Over Voltage	V <sub>STR</sub> OVP Flag SYS[3] bit	INT pin goes high	Converter stops switching.
V <sub>BUS</sub> Power Fail	V <sub>BUS</sub> Power Fail Flag SYS[2] bit	INT pin goes high BUSPG pin goes low	RBFET turns off. IC enters buck mode.
V <sub>IN</sub> Power Fail	V <sub>IN</sub> Power Fail Flag SYS[1] bit	INT pin goes high BUSPG pin goes low	RBFET turns off. IC enters buck mode.

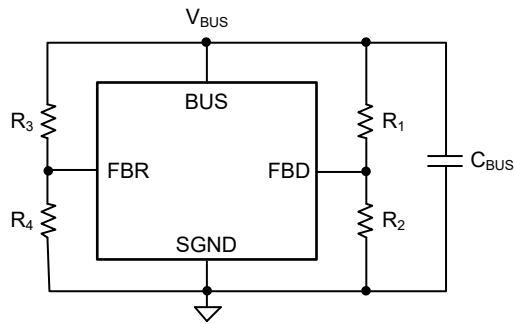
## APPLICATION INFORMATION

### Selecting Feedback Resistors

The SGM41664 enters buck mode and regulates the BUS voltage at  $V_{BUS\_REG}$  when  $V_{BUS}$  falls below  $V_{BUS\_DET}$  as shown in Figure 8. The BUSPG output will be low in buck mode. Figure 9 shows how the  $V_{BUS\_DET}$  and  $V_{BUS\_REG}$  values can be adjusted by  $R_1 - R_2$  and  $R_3 - R_4$  resistor dividers, respectively. It is recommended to set  $V_{BUS\_DET}$  lower than  $V_{BUS\_REG}$ .



**Figure 8. Buck Mode Waveforms**



**Figure 9.  $V_{BUS}$  Feedback Resistors**

It is recommended to choose 1% precision resistors for  $R_1$ ,  $R_2$ ,  $R_3$  and  $R_4$  in the 10k $\Omega$  to 1M $\Omega$  range to minimize the loss and for good light load efficiency. Equation 5 and 6 can be used to select the resistors.

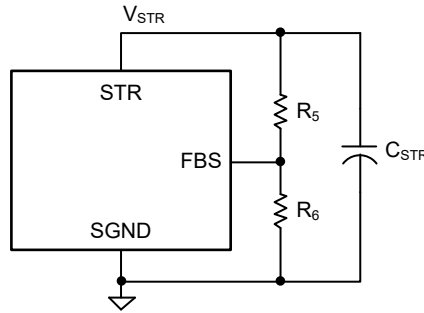
$$V_{BUS\_DET} = \frac{R_1 + R_2}{R_2} \times 0.6V \tag{5}$$

$$V_{BUS\_REG} = \frac{R_3 + R_4}{R_4} \times 0.6V \tag{6}$$

## APPLICATION INFORMATION (continued)

The boost charger stops working in burst mode, when  $V_{FBS}$  exceeds 1.2V and restarts again when  $V_{FBS}$  falls below 1.17V. Figure 10 shows how  $R_5$  and  $R_6$  set the maximum voltage ( $V_{STR\_MAX}$ ) in burst mode. 1% resistors in the 10kΩ to 1MΩ range are recommended for  $R_5$  and  $R_6$ . Use Equation 7 to select  $R_5$  and  $R_6$ .

$$V_{STR\_MAX} = \frac{R_5 + R_6}{R_6} \times 1.2V \quad (7)$$



**Figure 10.  $V_{STR}$  Feedback Resistor Divider**

If the boost charger operates in CV mode, Equation 8 can be used to set the desired  $V_{STR}$ .

$$V_{STR} = \frac{R_5 + R_6}{R_6} \times 1.2V \quad (8)$$

### Input Capacitor Selection ( $C_{IN}$ )

Two factors are considered for selecting  $C_{IN}$ :

1. It should tolerate the maximum input surge voltage with adequate margin.
2. The input peak current should be minimized to reduce the input noise. An extra 0.1μF or larger low ESR ceramic capacitor must be placed close to the IN pin for bypass.

The ceramic capacitors DC bias derating must be considered. Choose the X5R, X7R or better dielectrics for better DC bias and temperature stability. The DC bias effect is more significant for smaller sizes and choosing the largest possible size such as 1206 or 1210 is recommended. Consider a large margin for the voltage rating to cover the worst-case transients.

### BUS Capacitor Selection ( $C_{BUS}$ )

The  $C_{BUS}$  is the input capacitor of the boost charger and also the output capacitor of the converter in buck mode. The main factor for  $C_{BUS}$  selection is the stability of the control loop. Low ESR capacitors must be chosen for low ripple and small load step voltage transients.

For most applications, a 66μF or larger X5R or higher grade ceramic capacitor provides stable performance. Consider the actual capacitance value after bias voltage and temperature deratings.

### BD Capacitor Selection ( $C_{BD}$ )

The  $C_{BD}$  stores energy during boost pre-charge and releases that into  $C_{STR}$  when  $V_{STR} < V_{BD}$ . It is also the input port of the buck converter. A 2.2μF or larger low ESR ceramic capacitor is recommended for decoupling of the BD pin to PGND. Consider at least 20% higher voltage margin above the targeted storage voltage after capacitance derating.

## APPLICATION INFORMATION (continued)

### STR Capacitor Selection ( $C_{STR}$ )

The STR capacitor stores energy from  $V_{IN}$  during normal operation and releases it to the  $C_{BUS}$  when  $V_{IN}$  is lost. A general purpose electrolytic or a low profile POS capacitor is satisfactory in most applications. Consider 20% or more margin for the rated voltage. An additional 0.1 $\mu$ F or larger low ESR ceramic capacitor close to STR pin is necessary for decoupling. The  $C_{STR}$  bulk value is designed based on the required hold time for the application. The required storage capacitance can be calculated from Equation 9:

$$C_{STR} = \frac{2 \times V_{BUS\_REG} \times I_{BUS} \times t_{HOLD}}{\eta \times (V_{STR}^2 - V_{BUS\_REG}^2)} \quad (9)$$

$I_{BUS}$  is the BUS required current when it is regulated at  $V_{BUS\_REG}$ .

$V_{STR}$  is the storage voltage.

$t_{HOLD}$  is the required hold time.

$\eta$  is the energy-releasing efficiency of the buck. Consider the converter losses for  $C_{STR}$  design.

For example, if  $I_{BUS} = 3A$ ,  $t_{HOLD} = 20ms$ ,  $V_{STR} = 28V$ ,  $V_{BUS\_REG} = 7.5V$ , and  $\eta = 90\%$ , then  $C_{STR} (bulk) = 1374\mu F$ .

### Inductor Selection (L)

An inductor is necessary for the bidirectional DC/DC converter. Since the buck mode current is higher, the inductor is designed for the buck mode. If the maximum storage voltage is  $V_{STR\_MAX}$ , the BUS regulation voltage is  $V_{BUS\_REG}$  and the buck switching frequency is  $f_{SW}$ . The inductance is given by Equation 10:

$$L = \frac{V_{BUS\_REG}}{\Delta I_L f_{SW}} \left(1 - \frac{V_{BUS\_REG}}{V_{STR\_MAX}}\right) \quad (10)$$

where  $\Delta I_L$  is the peak-to-peak inductor ripple current and is typically selected between 20% to 40% of the full load current. The inductor saturation current should be higher than the inductor peak current with some margin.

### Bootstrap Capacitor ( $C_{BST}$ )

A bootstrap capacitor  $C_{BST}$  is needed for upper switch gate driver. A 0.1 $\mu$ F low ESR ceramic capacitor is recommended between BST and LX pins.

### Power-On Reset Delay Time

A 10nF or larger capacitor connected to the DLY pin sets the power-on reset delay time. If the DLY pin is left floating, a default delay, around 1.0ms will be applied. Table 2 lists the recommended capacitor values and the corresponding delay times.

**Table 2. Recommended  $C_{DLY}$  values for POR Delay  $t_{DLY}$**

$C_{DLY}$ (nF)	None	10	47	100
$t_{DLY}$ (ms)	1.0	2.5	11.8	25

### RBFET Soft-Start Time

A 10nF or larger capacitor connected to SS pin sets the RBFET soft-start time. If the SS pin is left floating, a 1ms default delay will apply. Table 3 lists the recommended capacitor values and the corresponding soft-start times.

**Table 3. Recommended  $C_{SS}$  Values and Soft-Start times**

$C_{SS}$ (nF)	None	10	47	100
$t_{SS}$ (ms)	1.0	2.1	9.7	20.6



# Efficient Power Backup Manager with High Current Bidirectional DC/DC Converter and Capacitor Measurement Capability

## SGM41664

### APPLICATION INFORMATION (continued)

#### PCB Layout Guidelines

A good PCB layout is critical for a stable design. Follow the following guidelines to design a good layout for SGM41664.

1. Use short, wide, and direct traces for high-current connections (IN, BUS, LX, BD, STR and PGND).
2. Keep the switching node (LX) trace short and away from BUS and feedback network traces.
3. Use decoupling capacitors close to the BUS and PGND pins.
4. Use decoupling capacitors close to the STR and PGND pins. If a bulk capacitor is used, add an additional 1µF ceramic capacitor or larger value as close as possible to the STR and PGND pins.
5. Use decoupling capacitors close to the VCC and AGND pins.
6. Place the feedback resistors close to the feedback pins that are sensitive to noise (FBD/FBR/FBS).
7. Keep the BST trace as short as possible to the device.
8. Connect all signal grounds together and connect them at only one point to the PGND.

### TYPICAL APPLICATION CIRCUIT

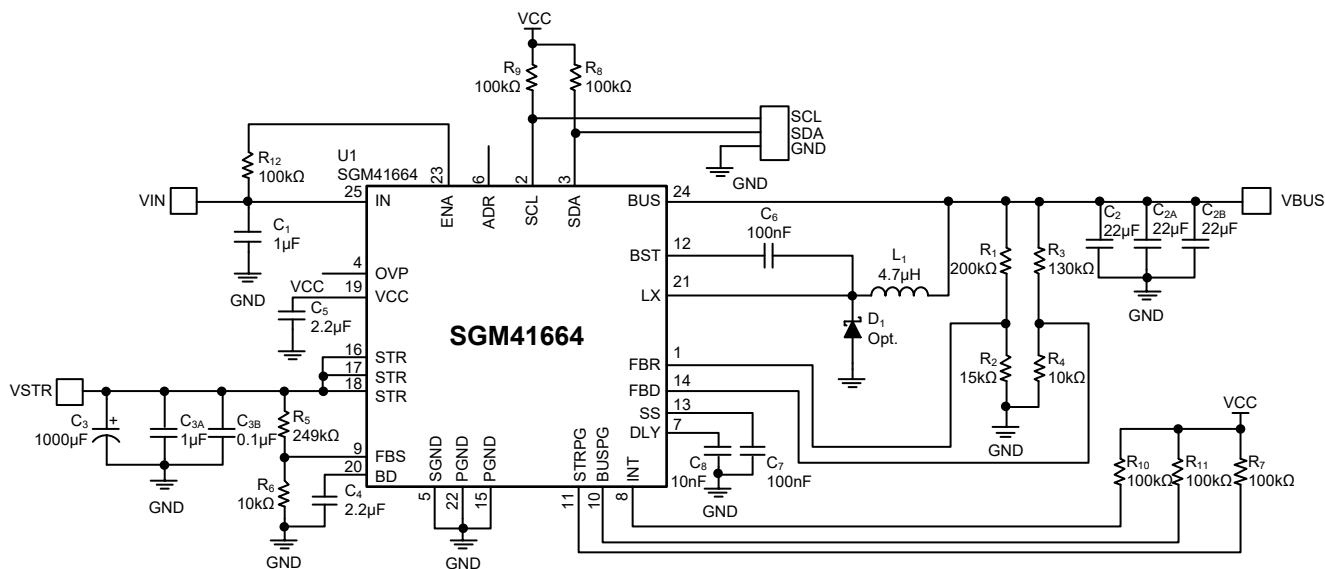
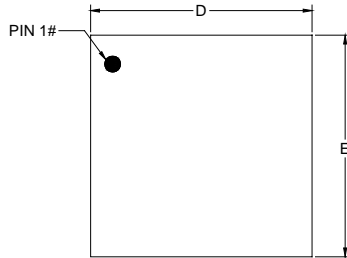


Figure 11. A Typical Power Back up Application Circuit with 12V Input and 31V Storage Voltage

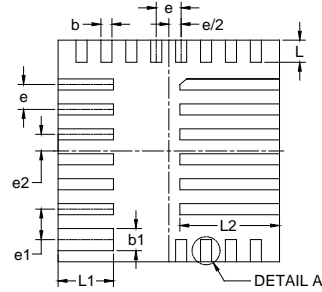
# PACKAGE INFORMATION

## PACKAGE OUTLINE DIMENSIONS

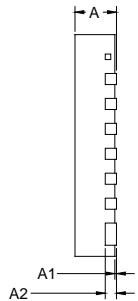
### TQFN-4x4-25L



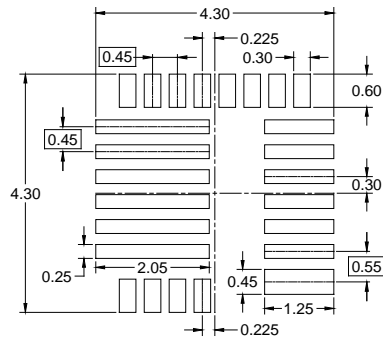
TOP VIEW



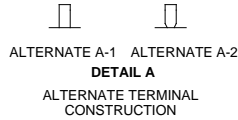
BOTTOM VIEW



SIDE VIEW



RECOMMENDED LAND PATTERN (Unit: mm)



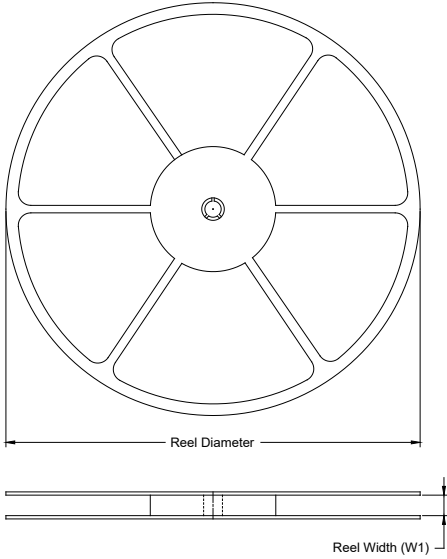
Symbol	Dimensions In Millimeters		
	MIN	MOD	MAX
A	0.700	0.750	0.800
A1	0.000	0.020	0.050
A2	0.203 REF		
b	0.150	0.200	0.250
b1	0.350	0.400	0.450
D	4.000 BSC		
E	4.000 BSC		
e	0.450 BSC		
e1	0.550 BSC		
e2	0.300 BSC		
L	0.300	0.400	0.500
L1	0.900	1.000	1.100
L2	1.700	1.800	1.900

NOTE: This drawing is subject to change without notice.

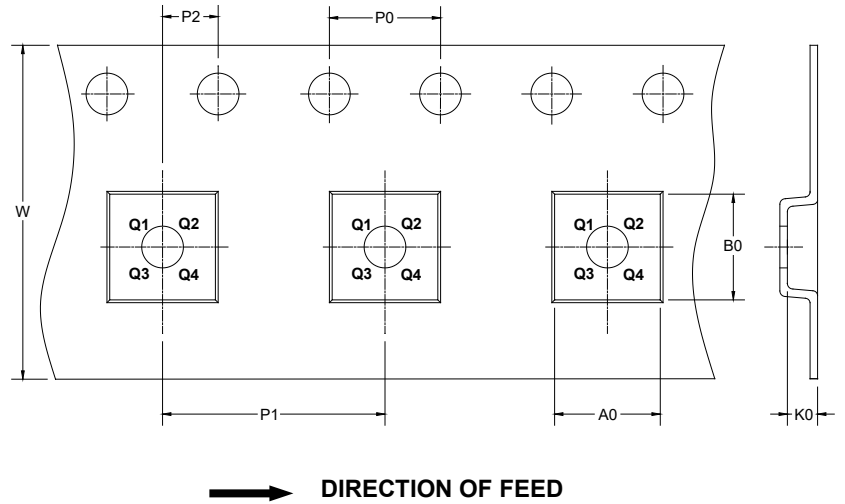
# PACKAGE INFORMATION

## TAPE AND REEL INFORMATION

### REEL DIMENSIONS



### TAPE DIMENSIONS



NOTE: The picture is only for reference. Please make the object as the standard.

### KEY PARAMETER LIST OF TAPE AND REEL

Package Type	Reel Diameter	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
TQFN-4×4-25L	13"	12.4	4.30	4.30	1.10	4.0	8.0	2.0	12.0	Q2

DD0001

# PACKAGE INFORMATION

## CARTON BOX DIMENSIONS



NOTE: The picture is only for reference. Please make the object as the standard.

## KEY PARAMETER LIST OF CARTON BOX

Reel Type	Length (mm)	Width (mm)	Height (mm)	Pizza/Carton
13"	386	280	370	5

DD0002